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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	48
Program Memory Size	96KB (96K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 12x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LFQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f101lfdfb-x0

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

Table 1-1. List of Ordering Part Numbers

(6/12)

Pin count	Package	Data flash	Fields of Application	Ordering Part Number
48 pins	48-pin plastic HWQFN (7 × 7 mm, 0.5 mm pitch)	Mounted	А	R5F100GAANA#U0, R5F100GCANA#U0, R5F100GDANA#U0, R5F100GEANA#U0, R5F100GFANA#U0, R5F100GGANA#U0, R5F100GHANA#U0, R5F100GJANA#U0, R5F100GKANA#U0,
				R5F100GLANA#U0
				R5F100GAANA#W0, R5F100GCANA#W0,
				R5F100GDANA#W0, R5F100GEANA#W0,
				R5F100GFANA#W0, R5F100GGANA#W0,
				R5F100GHANA#W0, R5F100GJANA#W0,
				R5F100GKANA#W0, R5F100GLANA#W0
			D	R5F100GADNA#U0, R5F100GCDNA#U0, R5F100GDDNA#U0,
				R5F100GEDNA#U0, R5F100GFDNA#U0, R5F100GGDNA#U0,
				R5F100GHDNA#U0, R5F100GJDNA#U0, R5F100GKDNA#U0,
				R5F100GLDNA#U0
				R5F100GADNA#W0, R5F100GCDNA#W0,
				R5F100GDDNA#W0, R5F100GEDNA#W0, R5F100GFDNA#W0, R5F100GGDNA#W0,
				R5F100GHDNA#W0, R5F100GJDNA#W0,
				R5F100GKDNA#W0, R5F100GLDNA#W0
			G	R5F100GAGNA#U0, R5F100GCGNA#U0, R5F100GDGNA#U0,
				R5F100GEGNA#U0, R5F100GFGNA#U0, R5F100GGGNA#U0,
				R5F100GHGNA#U0, R5F100GJGNA#U0
				R5F100GAGNA#W0, R5F100GCGNA#W0,
				R5F100GDGNA#W0, R5F100GEGNA#W0,
				R5F100GFGNA#W0, R5F100GGGNA#W0,
				R5F100GHGNA#W0, R5F100GJGNA#W0
		Not	Α	R5F101GAANA#U0, R5F101GCANA#U0, R5F101GDANA#U0,
		mounted		R5F101GEANA#U0, R5F101GFANA#U0, R5F101GGANA#U0,
				R5F101GHANA#U0, R5F101GJANA#U0, R5F101GKANA#U0,
				R5F101GLANA#U0
				R5F101GAANA#W0, R5F101GCANA#W0,
				R5F101GDANA#W0, R5F101GEANA#W0,
				R5F101GFANA#W0, R5F101GGANA#W0,
				R5F101GHANA#W0, R5F101GJANA#W0,
				R5F101GKANA#W0, R5F101GLANA#W0
			D	R5F101GADNA#U0, R5F101GCDNA#U0, R5F101GDDNA#U0,
				R5F101GEDNA#U0, R5F101GFDNA#U0, R5F101GGDNA#U0,
				R5F101GHDNA#U0, R5F101GJDNA#U0, R5F101GKDNA#U0,
				R5F101GLDNA#U0
				R5F101GADNA#W0, R5F101GCDNA#W0,
				R5F101GDDNA#W0, R5F101GEDNA#W0,
				R5F101GFDNA#W0, R5F101GGDNA#W0,
				R5F101GHDNA#W0, R5F101GJDNA#W0,
				R5F101GKDNA#W0, R5F101GLDNA#W0

Note For the fields of application, refer to Figure 1-1 Part Number, Memory Size, and Package of RL78/G13.

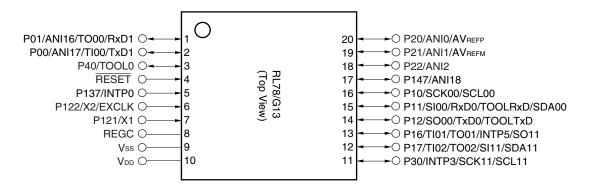
Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.



1.3 Pin Configuration (Top View)

1.3.1 20-pin products

• 20-pin plastic LSSOP (7.62 mm (300), 0.65 mm pitch)



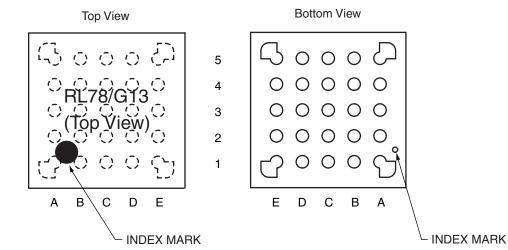
Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remark For pin identification, see 1.4 Pin Identification.

1.3.3 25-pin products

<R>

• 25-pin plastic WFLGA (3 × 3 mm, 0.50 mm pitch)



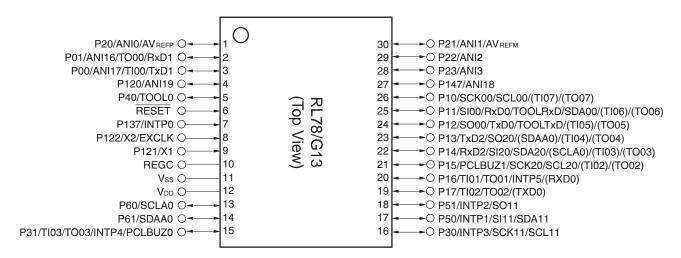
	Α	В	С	D	E	
5	P40/TOOL0	RESET	P01/ANI16/ TO00/RxD1	P22/ANI2	P147/ANI18	5
4	P122/X2/ EXCLK	P137/INTP0	P00/ANI17/ TI00/TxD1	P21/ANI1/ AV _{REFM}	P10/SCK00/ SCL00	4
3	P121/X1	V _{DD}	P20/ANI0/ AV _{REFP}	P12/SO00/ TxD0/ TOOLTxD	P11/SI00/ RxD0/ TOOLRxD/ SDA00	3
2	REGC	Vss	P30/INTP3/ SCK11/SCL11	P17/TI02/ TO02/SO11	P50/INTP1/ SI11/SDA11	2
1	P60/SCLA0	P61/SDAA0	P31/TI03/ TO03/INTP4/ PCLBUZ0	P16/TI01/ TO01/INTP5	P130	1
	A	В	С	D	E	

Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remark For pin identification, see **1.4 Pin Identification**.

1.3.4 30-pin products

• 30-pin plastic LSSOP (7.62 mm (300), 0.65 mm pitch)

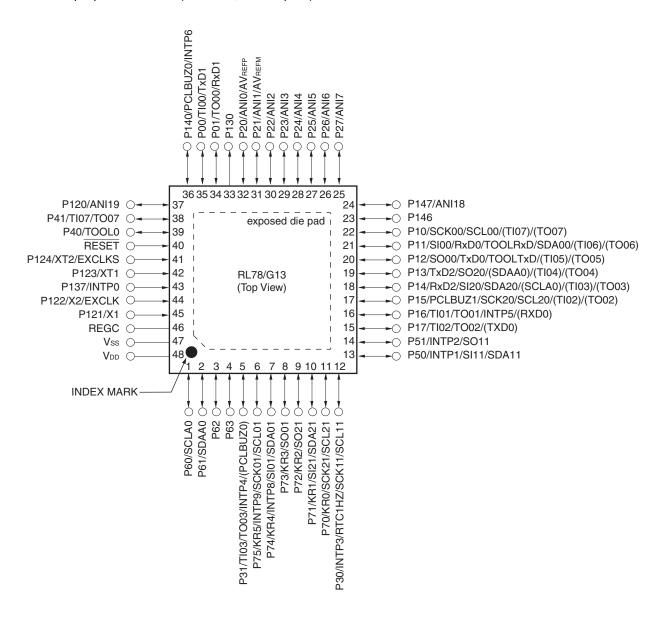


Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.

• 48-pin plastic HWQFN (7 × 7 mm, 0.5 mm pitch)



Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

- Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.
- 3. It is recommended to connect an exposed die pad to $V_{\rm ss.}$

1.4 Pin Identification

ANI0 to ANI14, REGC: Regulator capacitance RESET: ANI16 to ANI26: Reset Analog input AVREFM: A/D converter reference RTC1HZ: Real-time clock correction clock potential (- side) input (1 Hz) output AVREFP: A/D converter reference RxD0 to RxD3: Receive data potential (+ side) input SCK00, SCK01, SCK10, EVDD0, EVDD1: Power supply for port SCK11, SCK20, SCK21, EVsso, EVss1: Ground for port SCLA0, SCLA1: Serial clock input/output EXCLK: External clock input (Main SCLA0, SCLA1, SCL00, SCL01, SCL10, SCL11, system clock) **EXCLKS**: External clock input SCL20, SCL21, SCL30, (Subsystem clock) SCL31: Serial clock output INTP0 to INTP11: Interrupt request from SDAA0, SDAA1, SDA00, peripheral SDA01, SDA10, SDA11, KR0 to KR7: Key return SDA20,SDA21, SDA30, P00 to P07: Port 0 SDA31: Serial data input/output P10 to P17: Port 1 SI00, SI01, SI10, SI11, P20 to P27: Port 2 SI20, SI21, SI30, SI31: Serial data input P30 to P37: Port 3 SO00, SO01, SO10, P40 to P47: Port 4 SO11, SO20, SO21, P50 to P57: Port 5 SO30, SO31: Serial data output P60 to P67: Port 6 TI00 to TI07, P70 to P77: Port 7 TI10 to TI17: Timer input P80 to P87: Port 8 TO00 to TO07. P90 to P97: Port 9 TO10 to TO17: Timer output P100 to P106: Port 10 TOOL0: Data input/output for tool P110 to P117: Port 11 TOOLRxD, TOOLTxD: Data input/output for external device P120 to P127: Port 12 TxD0 to TxD3: Transmit data P130, P137: Port 13 V_{DD}: Power supply P140 to P147: Port 14 Vss: Ground P150 to P156: Port 15 X1, X2: Crystal oscillator (main system clock) PCLBUZ0, PCLBUZ1: Programmable clock XT1, XT2: Crystal oscillator (subsystem clock) output/buzzer output

 The number of PWM outputs varies depending on the setting of channels in use (the number of masters and slaves) (see 6.9.3 Operation as multiple PWM output function in the RL78/G13 User's Manual).

(2/2)

							(2/2)			
Ite	m	80-	pin	100	-pin	128	3-pin			
		R5F100Mx	R5F101Mx	R5F100Px	R5F101Px	R5F100Sx AHz 16.384 kHz, 32.76 26 channels ting LIN-bus): 1 cl 2 channels	R5F101Sx			
Clock output/buzz	er output		2	1	2		2			
		• 2.44 kHz, 4.8	8 kHz, 9.76 kHz,	1.25 MHz, 2.5 M	Hz, 5 MHz, 10 M	ИHz				
		· ·	clock: fmain = 20							
						16.384 kHz, 32.76	68 kHz			
0/40 1 "	A /D		CIOCK: ISUB = 32.70	68 kHz operation)		I				
8/10-bit resolution	A/D converter	17 channels		20 channels		26 channels				
Serial interface		[80-pin, 100-pin, 128-pin products]								
			•	2 channels/UAR						
				2 channels/UAR		tina I IN-hus): 1 (channel			
		 CSI: 2 channels/simplified l²C: 2 channels/UART (UART supporting LIN-bus): 1 channel CSI: 2 channels/simplified l²C: 2 channels/UART: 1 channel 								
	I ² C bus	2 channels	·	2 channels		2 channels				
Multiplier and divid	der/multiply-	• 16 bits × 16 bits = 32 bits (Unsigned or signed)								
accumulator		• 32 bits ÷ 32 bi	2 bits = 32 bits (Unsigned)							
		• 16 bits × 16 bits	6 bits \times 16 bits + 32 bits = 32 bits (Unsigned or signed)							
DMA controller		4 channels								
Vectored	Internal		37	3	37		41			
interrupt sources	External		13	1	3		13			
Key interrupt			8	1	8		8			
Reset		Reset by RES								
			by watchdog tim							
			by power-on-res by voltage detec							
				tion execution Note						
			by RAM parity e							
			by illegal-memor							
Power-on-reset cir	rcuit	Power-on-res	et: 1.51 V (TY	P.)						
		Power-down-	reset: 1.50 V (TY	P.)						
Voltage detector		Rising edge :		.06 V (14 stages))					
		Falling edge:	1.63 V to 3	3.98 V (14 stages)	1					
On-chip debug fur	nction	Provided								
Power supply volta	age	$V_{DD} = 1.6 \text{ to } 5.5 \text{ V } (T_A = -40 \text{ to } +85^{\circ}\text{C})$								
		$V_{DD} = 2.4 \text{ to } 5.5$	$V (T_A = -40 \text{ to } +1)$	05°C)						
Operating ambien	t temperature	$T_A = 40 \text{ to } +85^\circ$	C (A: Consumer	applications, D: Ir	ndustrial applicat	ions)				
		$T_A = 40 \text{ to } +105$	°C (G: Industrial	applications)						
		1								



Note The illegal instruction is generated when instruction code FFH is executed.

Reset by the illegal instruction execution not issued by emulation with the in-circuit emulator or on-chip debug emulator.



(3) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output) $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \leq \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

Parameter	Symbol	C	Conditions	HS (high main)	•	LS (low main)	•	LV (low- main)	-voltage Mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkcy1	tксү1 ≥ 4/fс∟к	$2.7~V \leq EV_{DD0} \leq 5.5$ V	125		500		1000		ns
			$2.4~V \leq EV_{DD0} \leq 5.5$ V	250		500		1000		ns
			$1.8~V \le EV_{DD0} \le 5.5$ V	500		500		1000		ns
			$1.7~V \le EV_{DD0} \le 5.5$ V	1000		1000		1000		ns
			$1.6~V \le EV_{DD0} \le 5.5$ V	_		1000		1000		ns
SCKp high-/low-level width	tkhi, tkli	4.0 V ≤ EV _D	00 ≤ 5.5 V	tксү1/2 – 12		tксу1/2 — 50		tксү1/2 – 50		ns
		$2.7~\text{V} \leq \text{EV}_{\text{DD0}} \leq 5.5~\text{V}$		tксү1/2 – 18		tксу1/2 — 50		tксү1/2 – 50		ns
		2.4 V ≤ EV _D	$2.4~V \leq EV_{DD0} \leq 5.5~V$			tксу1/2 — 50		tксү1/2 — 50		ns
	1.8 V	1.8 V ≤ EV _D	$1.8~V \leq EV_{DD0} \leq 5.5~V$			tксү1/2 — 50		tксү1/2 – 50		ns
		1.7 V ≤ EV _D	00 ≤ 5.5 V	tксу1/2 — 100		tксу1/2 — 100		tксу1/2 — 100		ns
		$1.6~V \leq EV_{DD0} \leq 5.5~V$		_		tксу1/2 — 100		tксу1/2 — 100		ns
SIp setup time	tsıĸı	4.0 V ≤ EV _{DI}	00 ≤ 5.5 V	44		110		110		ns
(to SCKp↑)		2.7 V ≤ EV _{DI}	00 ≤ 5.5 V	44		110		110		ns
		2.4 V ≤ EV _{DI}	00 ≤ 5.5 V	75		110		110		ns
		1.8 V ≤ EV _{DI}	oo ≤ 5.5 V	110		110		110		ns
		1.7 V ≤ EV _{DI}	oo ≤ 5.5 V	220		220		220		ns
		1.6 V ≤ EV _{DI}	oo ≤ 5.5 V	_		220		220		ns
SIp hold time	tksi1	1.7 V ≤ EV _{DI}	00 ≤ 5.5 V	19		19		19		ns
(from SCKp↑) Note 2		1.6 V ≤ EV _{DI}	00 ≤ 5.5 V	_		19		19		ns
Delay time from SCKp↓ to SOp	tkso1	$1.7 \text{ V} \le \text{EV}_{DI}$ $C = 30 \text{ pF}^{\text{Note}}$			25		25		25	ns
output Note 3		$1.6 \text{ V} \leq \text{EV}_{DI}$ $C = 30 \text{ pF}^{\text{Note}}$			_		25		25	ns

Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

- 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- 4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

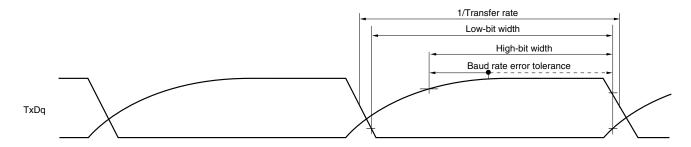
(5) During communication at same potential (simplified I²C mode) (1/2)

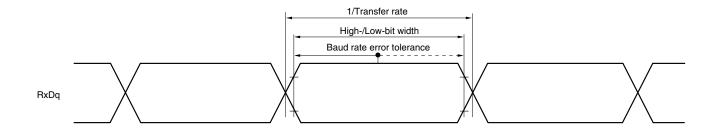
(Ta = -40 to +85°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V)

Parameter	Symbol	Conditions	` `	h-speed Mode	`	v-speed Mode	`	-voltage Mode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLr clock frequency	fscL	$2.7~V \leq EV_{DD0} \leq 5.5~V,$ $C_b = 50~pF,~R_b = 2.7~k\Omega$		1000 Note 1		400 Note 1		400 Note 1	kHz
		$1.8~V \leq EV_{DD0} \leq 5.5~V,$ $C_b = 100~pF,~R_b = 3~k\Omega$		400 Note 1		400 Note 1		400 Note 1	kHz
		1.8 V \leq EV _{DD0} $<$ 2.7 V, C _b = 100 pF, R _b = 5 kΩ		300 Note 1		300 Note 1		300 Note 1	kHz
		$1.7 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V},$ $C_b = 100 \text{ pF}, R_b = 5 \text{ k}\Omega$		250 Note 1		250 Note 1		250 Note 1	kHz
		1.6 V \leq EV _{DD0} $<$ 1.8 V, C _b = 100 pF, R _b = 5 kΩ		_		250 Note 1		250 Note 1	kHz
Hold time when SCLr = "L"	tLOW	$2.7~V \leq EV_{DD0} \leq 5.5~V,$ $C_b = 50~pF,~R_b = 2.7~k\Omega$	475		1150		1150		ns
		$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$ $C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$	1150	150 115	1150		1150		ns
		$1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 2.7 \text{ V},$ $C_b = 100 \text{ pF}, R_b = 5 \text{ k}\Omega$	1550		1550		1550		ns
		$1.7 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V},$ $C_b = 100 \text{ pF}, R_b = 5 \text{ k}\Omega$	1850		1850		1850		ns
		$1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V},$ $C_b = 100 \text{ pF}, R_b = 5 \text{ k}\Omega$	_		1850		1850		ns
Hold time when SCLr = "H"	tніgн	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$	475		1150		1150		ns
		1.8 V \leq EV _{DD0} \leq 5.5 V, C _b = 100 pF, R _b = 3 kΩ	1150		1150		1150		ns
		$1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 2.7 \text{ V},$ $C_b = 100 \text{ pF}, R_b = 5 \text{ k}\Omega$	1550		1550		1550		ns
		$1.7 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V},$ $C_b = 100 \text{ pF}, R_b = 5 \text{ k}\Omega$	1850		1850		1850		ns
		$1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V},$ $C_b = 100 \text{ pF}, R_b = 5 \text{ k}\Omega$	_		1850		1850		ns

(Notes and Caution are listed on the next page, and Remarks are listed on the page after the next page.)

UART mode bit width (during communication at different potential) (reference)





- $\begin{tabular}{ll} \begin{tabular}{ll} \bf R_b[\Omega]: Communication line (TxDq) pull-up resistance, \\ C_b[F]: Communication line (TxDq) load capacitance, V_b[V]: Communication line voltage \\ \end{tabular}$
 - 2. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)
 - 3. fmck: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))
 - **4.** UART2 cannot communicate at different potential when bit 1 (PIOR1) of peripheral I/O redirection register (PIOR) is 1.

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (1/3)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

Parameter	Symbol		Conditions	HS (hig	h-speed Mode	LS (low	r-speed Mode		-voltage Mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkcy1	tkcy1 ≥ 4/fclk	$\begin{split} 4.0 & \ V \leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 & \ V \leq V_b \leq 4.0 \ V, \\ C_b = 30 & \ pF, \ R_b = 1.4 \ k\Omega \end{split}$	300		1150		1150		ns
			$\begin{split} 2.7 \ V & \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V & \leq V_b \leq 2.7 \ V, \\ C_b & = 30 \ pF, \ R_b = 2.7 \ k\Omega \end{split}$	500		1150		1150		ns
			$\begin{aligned} 1.8 \ V &\leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V &\leq V_b \leq 2.0 \ V^{Note}, \end{aligned}$	1150		1150		1150		ns
SCKp high-level width	gh-level tkH1 $4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V}$,	tксү1/2 – 75		tксү1/2 – 75		tксу1/2 — 75		ns
		$2.7 \text{ V} \le \text{EV}_{DD}$ $2.3 \text{ V} \le \text{V}_{b} \le$ $C_{b} = 30 \text{ pF},$	00 < 4.0 V, 2.7 V,	tксу1/2 — 170		tксу1/2 — 170		tксу1/2 — 170		ns
		$1.8 \text{ V} \le \text{EV}_{DD}$ $1.6 \text{ V} \le \text{V}_{b} \le \text{C}_{b} = 30 \text{ pF},$	00 < 3.3 V, 2.0 V ^{Note} ,	tксү1/2 – 458		tксү1/2 – 458		tксү1/2 – 458		ns
SCKp low-level width	t _{KL1}	$4.0 \text{ V} \leq \text{EV}_{DD}$ $2.7 \text{ V} \leq \text{V}_{b} \leq$	00 ≤ 5.5 V, 4.0 V,	tксу1/2 —		tксү1/2 — 50		tксү1/2 — 50		ns
		$C_b = 30 \text{ pF},$ $2.7 \text{ V} \leq \text{EVor}$ $2.3 \text{ V} \leq \text{V}_b \leq$ $C_b = 30 \text{ pF},$	00 < 4.0 V, 2.7 V,	tксү1/2 — 18		tксү1/2 — 50		tксү1/2 — 50		ns
		$1.8 \text{ V} \leq \text{EV}_{DD}$ $1.6 \text{ V} \leq \text{V}_{b} \leq$ $C_{b} = 30 \text{ pF},$	00 < 3.3 V, 2.0 V ^{Note} ,	tксү1/2 — 50		tксү1/2 – 50		tксу1/2 — 50		ns

Note Use it with $EV_{DD0} \ge V_b$.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (When 20- to 52-pin products)/EVDD tolerance (When 64- to 128-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed two pages after the next page.)

2.6.5 Power supply voltage rising slope characteristics

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	Svdd				54	V/ms

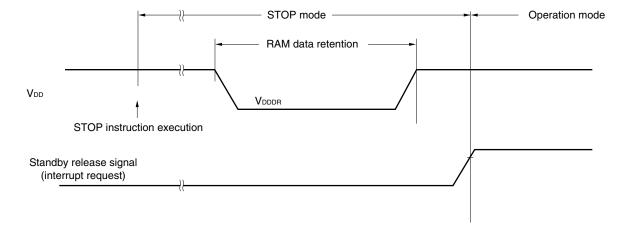
Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until V_{DD} reaches the operating voltage range shown in 2.4 AC Characteristics.

2.7 RAM Data Retention Characteristics

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	V _{DDDR}		1.46 ^{Note}		5.5	٧

Note This depends on the POR detection voltage. For a falling voltage, data in RAM are retained until the voltage reaches the level that triggers a POR reset but not once it reaches the level at which a POR reset is generated.



2.8 Flash Memory Programming Characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
CPU/peripheral hardware clock frequency	fclk	$1.8~V \leq V \text{dd} \leq 5.5~V$	1		32	MHz
Number of code flash rewrites	Cerwr	Retained for 20 years TA = 85°C	1,000			Times
Number of data flash rewrites		Retained for 1 years TA = 25°C		1,000,000		
		Retained for 5 years TA = 85°C	100,000			
		Retained for 20 years TA = 85°C	10,000			

Notes 1. 1 erase + 1 write after the erase is regarded as 1 rewrite.

- The retaining years are until next rewrite after the rewrite.
- 2. When using flash memory programmer and Renesas Electronics self programming library
- **3.** These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.

2.9 Dedicated Flash Memory Programmer Communication (UART)

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200	_	1,000,000	bps

- Notes 1. Total current flowing into VDD and EVDDO, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDDO or Vss, EVsso. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 3. When high-speed system clock and subsystem clock are stopped.
 - **4.** When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 - **5.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: $2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V} @ 1 \text{ MHz}$ to 32 MHz $2.4 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V} @ 1 \text{ MHz}$ to 16 MHz

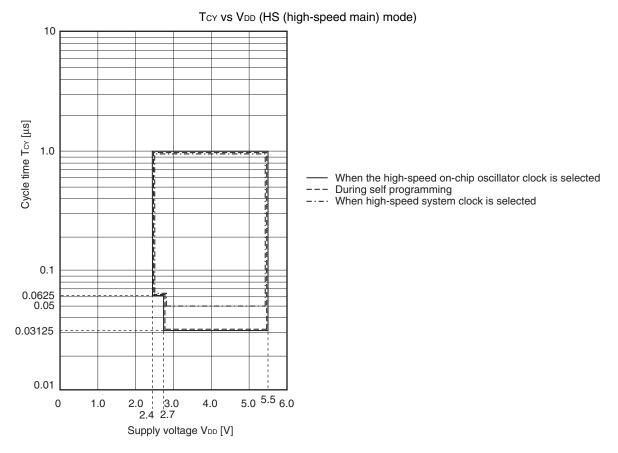
- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 4. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C

- Notes 1. Total current flowing into VDD, EVDDO, and EVDD1, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDDO, and EVDD1, or Vss, EVSSO, and EVSS1. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. During HALT instruction execution by flash memory.
 - 3. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 4. When high-speed system clock and subsystem clock are stopped.
 - **5.** When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
 - 6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 - 7. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

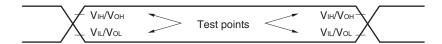
HS (high-speed main) mode: $2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V} @ 1 \text{ MHz}$ to 32 MHz $2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V} @ 1 \text{ MHz}$ to 16 MHz

- 8. Regarding the value for current operate the subsystem clock in STOP mode, refer to that in HALT mode.
- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - **4.** Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is $T_A = 25^{\circ}C$

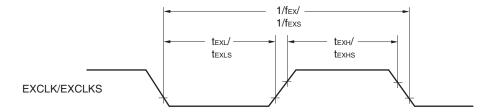
Minimum Instruction Execution Time during Main System Clock Operation



AC Timing Test Points



External System Clock Timing



(3) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input) $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

Parameter	Symbol	Cond	ditions	HS (high-speed ma	in) Mode	Unit
				MIN.	MAX.	
SCKp cycle time Note 5	tkcy2	$4.0~V \leq EV_{DD0} \leq 5.5$	20 MHz < fмск	16/fмск		ns
		V	fмcк ≤ 20 MHz	12/fмск		ns
		$2.7~V \leq EV_{DD0} \leq 5.5$ V	16 MHz < fмск	16/fмск		ns
			fмck ≤ 16 MHz	12/fмск		ns
		2.4 V ≤ EV _{DD0} ≤ 5.5 V		16/fмск		ns
				12/fмcк and 1000		ns
SCKp high-/low-level	t кн2,	$4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ M}$	V	tkcy2/2 – 14		ns
width	t _{KL2}	2.7 V ≤ EV _{DD0} ≤ 5.5 V		tkcy2/2 – 16		ns
		2.4 V ≤ EV _{DD0} ≤ 5.5	V	tkcy2/2 - 36	,	ns
SIp setup time	tsık2	$2.7~V \leq EV_{DD0} \leq 5.5$	V	1/fмск+40		ns
(to SCKp↑) Note 1		$2.4~V \leq EV_{DD0} \leq 5.5$	V	1/fмск+60	2/fмcк+66	ns
SIp hold time (from SCKp↑) Note 2	tksi2	2.4 V ≤ EV _{DD0} ≤ 5.5	V	1/fмск+62		ns
Delay time from SCKp↓ to SOp output	tkso2	C = 30 pF Note 4	$2.7~V \leq EV_{DD0} \leq 5.5$ V		2/fмск+66	ns
Note 3			$2.4~V \leq EV_{DD0} \leq 5.5$ V		2/fмск+113	ns

- **Notes 1.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 4. C is the load capacitance of the SOp output lines.
 - 5. Transfer rate in the SNOOZE mode: MAX. 1 Mbps

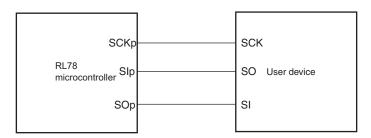
Caution Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

- **Remarks 1.** p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM number (g = 0, 1, 4, 5, 8, 14)
 - 2. fmck: Serial array unit operation clock frequency

 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

 n: Channel number (mn = 00 to 03, 10 to 13))

CSI mode connection diagram (during communication at same potential)



(4) During communication at same potential (simplified I²C mode)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
SCLr clock frequency	fscL	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$		400 Note1	kHz
		$C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$			
		$2.4 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$		100 Note1	kHz
		$C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$			
Hold time when SCLr = "L"	tLow	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$	1200		ns
		$C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$			
		$2.4 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$	4600		ns
		$C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$			
Hold time when SCLr = "H"	tніgн	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$	1200		ns
		$C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$			
		$2.4 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$	4600		ns
		$C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$			
Data setup time (reception)	tsu:dat	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$	1/f _{MCK} + 220 Note2		ns
		$C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$			
		$2.4 \text{ V} \leq \text{EV}_{DD} \leq 5.5 \text{ V},$	1/fmck + 580 Note2		ns
		$C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$			
Data hold time (transmission)	thd:dat	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$	0	770	ns
		$C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$			
		$2.4 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$	0	1420	ns
		$C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$			

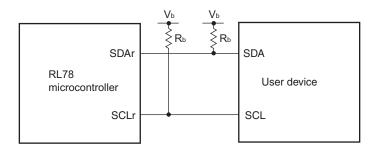
Notes 1. The value must also be equal to or less than fmck/4.

2. Set the fmck value to keep the hold time of SCLr = "L" and SCLr = "H".

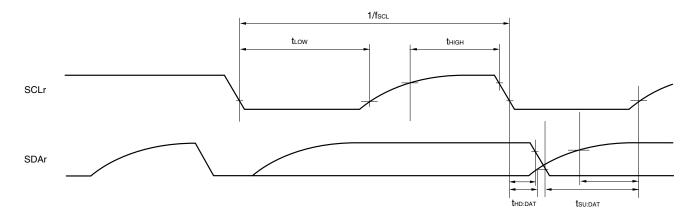
Caution Select the normal input buffer and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).

(Remarks are listed on the next page.)

Simplified I²C mode connection diagram (during communication at different potential)



Simplified I²C mode serial transfer timing (during communication at different potential)



Caution Select the TTL input buffer and the N-ch open drain output (VDD tolerance (for the 20- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the SDAr pin and the N-ch open drain output (VDD tolerance (for the 20- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VH and VIL, see the DC characteristics with TTL input buffer selected.

- **Remarks 1.** R_b[Ω]:Communication line (SDAr, SCLr) pull-up resistance, C_b[F]: Communication line (SDAr, SCLr) load capacitance, V_b[V]: Communication line voltage
 - 2. r: IIC number (r = 00, 01, 10, 20, 30, 31), g: PIM, POM number (g = 0, 1, 4, 5, 8, 14)
 - 3. fmck: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,n: Channel number (mn = 00, 01, 02, 10, 12, 13)

4.11 64-pin Products

R5F100LCAFA, R5F100LDAFA, R5F100LEAFA, R5F100LFAFA, R5F100LGAFA, R5F100LHAFA, R5F100LJAFA, R5F100LKAFA, R5F100LLAFA

R5F101LCAFA, R5F101LDAFA, R5F101LEAFA, R5F101LFAFA, R5F101LGAFA, R5F101LHAFA, R5F101LJAFA, R5F101LKAFA, R5F101LLAFA

R5F100LCDFA, R5F100LDDFA, R5F100LEDFA, R5F100LFDFA, R5F100LGDFA, R5F100LHDFA, R5F100LJDFA, R5F100LKDFA, R5F100LLDFA

R5F101LCDFA, R5F101LDDFA, R5F101LEDFA, R5F101LFDFA, R5F101LGDFA, R5F101LHDFA, R5F101LJDFA, R5F101LKDFA, R5F101LLDFA

Previous Code

MASS (TYP.) [g]

R5F100LCGFA, R5F100LDGFA, R5F100LEGFA, R5F100LFGFA, R5F100LGGFA, R5F100LHGFA, R5F100LJGFA

RENESAS Code

JEITA Package Code

